



Industrial Computing Platform Partner

GENE-6350

Thermal Image Analysis Report

Report No:05E080025

Release Date: 09 /27/ 2005

2005-09-27

Issue Stamp

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Manager

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Test Engineer

I . Model Name: GENE-6350 A1.1

II . Description:

Intel ULV Celeron Subcompact Board With LCD / Ethernet / Audio / CFD /Mini PCI / 4COMs / 4USBs / DVI

III . Date: 09 / 27 / 2005

IV . Measure Site: AAEON QE Dept.

V . Issued by: Liping Hsieh

VI.Equipment:

1. TVS-100 series by NIPPON AVIONICS CO., LTD.

VII. Simulation Environment:

• **Temperature:**

Component Side – 1:26.3 degrees C

Component Side – 2:26.6 degrees C

• **System Configuration :**

BIOS ver :A0.5

CPU: INTEL LV CELERON 650MHZ

Memory: TRANSCEND /V58C2256804SCT6/256MB

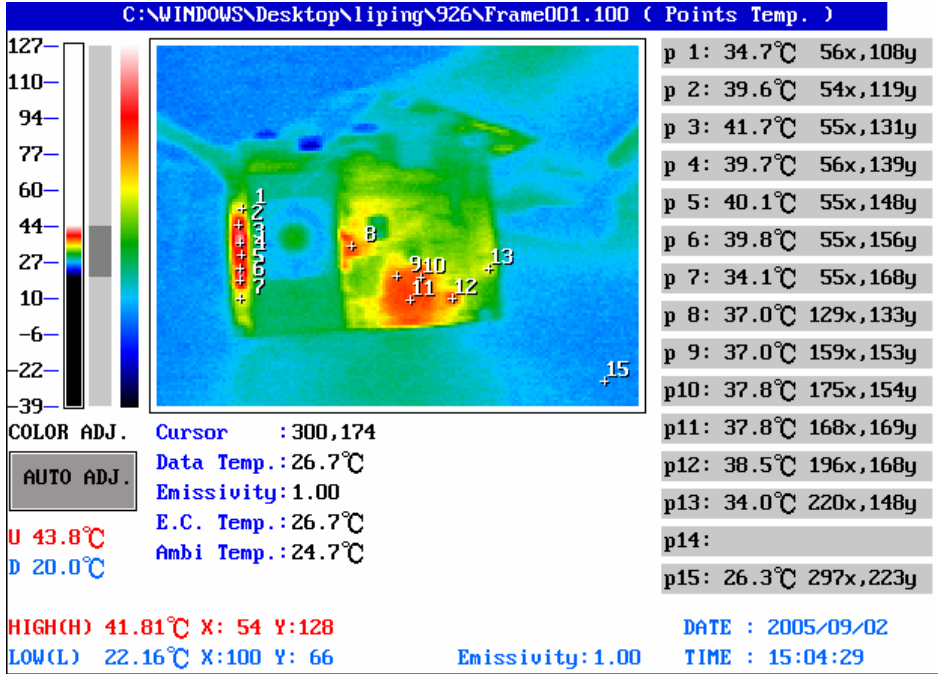
HDD: MAXTOR 80GB

• **Application Software: Windows 2000 run HCT9.5**

• **Take Picture Time: Power on 2 hours after**

Temperature Profile Test:

Component Side – 1:



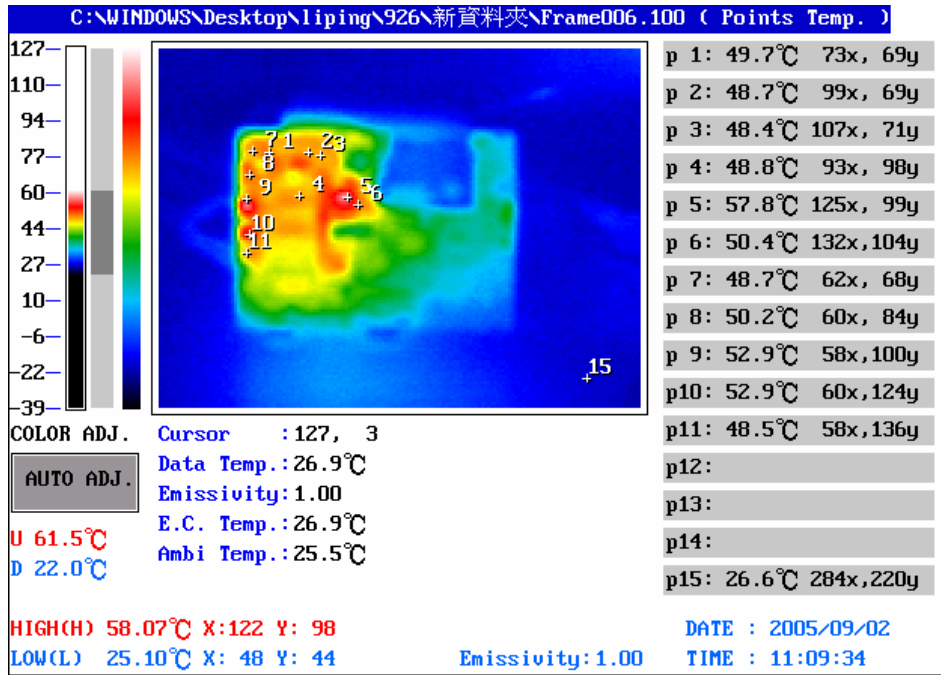
Point	Position	Describe	Tc	Tm (25°C)	Tm (60°C)	Note
1	C117	TDK/C1210-SERIES/YORKIE/MCC22uF+80/-20% 1210;EE-A000193;1129722090;TWN	-30°C~85°C	34.7°C	69.7°C	
2	U8	IC.SMD.SO-8P.Dual Operational Amplifiers.NS.LMV358M	150°C	39.6°C	74.6°C	
3	C304	KO-CAP.330uF.6.3V.20%.D(7.3*4.3*2.8mm).45mOhm SMD.KEMET.T520D337M006AS	105°C	41.7°C	76.7°C	
4	U4	APEC/AP4880M/PWR.SMD.SO-8N-Channel25V13A MOSFET.APEC.AP4880M;EE-A031081;1315488010;TWN	-55°C~150°C	39.7°C	74.7°C	
5	U5	APEC/AP4880M/PWR.SMD. SO-8N-Channel25V13A MOSFET.APEC.AP4880M;EE-A031081;1315488010;TWN	-55°C~150°C	40.1°C	75.1°C	
6	L5	(TF)INDUCTORS.1.6uH 11A.30%. SMD.2pin.GOTREND.GSCDK106P-1R6N; EE-A031086;1211101660;TWN	-40°C~85°C	39.8°C	74.8°C	
7	C17	Japan Carlit/SANMOS/SW Series/PC-CON. (100~220)uF.(2,2.5,4,6,3)V.20%.D(7.3*4.3*2.7mm).10mOhm SMD. Japan Carlit.SW Series;EE-A030626;	-55°C~105°C	34.1°C	69.1°C	
8	U9	IC.SMD.SSOP 48P.FTG for VIA Pro-266 DDR. CYPRESS.W311.ITX-266;EE-A040206;14S3031100;TWN	-30°C~100°C	37.0°C	72°C	
9	U10	IC.SMD.LQFP 100P.PCI Ethernet CHIP.RELTEK.RTL8100BL	-30°C~100°C	37.0°C	72°C	
10	U11	Winbond/W83781D/WINBOND STATUS MONITORING ICW83781D48PIN LQFP/87.09.22;EE-A980268;14S4378100;TWN	--40°C~120°C	37.8°C	72.8°C	
11	U2	VIA/VT8235/IC.SMD.BGA 487P. SouthBridgeChipset.VIA.VT8235;EE-A040476;14S4823500;TWN	0°C~85°C	37.8°C	72.8°C	
12	U1	IC.SMD LQFP 48Pin.6 Channel AC'97 Audio Codec.REALTEK.ALC650	0°C~85°C	38.5°C	73.5°C	
13	L6	(TF)INDUCTORS.3.3uH 6.5A.20%.SMD 2pin.AG.SMTDR105N-3R3M;EE-A030329;1211103362;TWN	-25°C~85°C	34.0°C	69°C	
14						
15		Ambient Temperature		26.3°C		

1. Operation Temperature (°C):

$$T_c(\text{Case temp.}) = T_a(\text{Ambient Temp.}) + /-30^\circ\text{C} = T_j(\text{Junction Temp.}) - /+25^\circ\text{C}$$

Note: The description in red states which temperature is over the specification of the device.

Component Side -2:



Thermal Image Analysis

Point	Position	Describe	Tc	Tm (25°C)	Tm (60°C)	Note
1	C241	(TF)SPCAP.(8.2~150)uF.(2,2.5,4,6.3,8,12.5,16)V.20%.D.SMD.Pansonic.EEFCD Series;EE-A020599;118*6***8*;TWN	-40°C~105°C	49.7°C	84.7°C	
2	C242	Japan Carlit/SANMOS/SW Series/PC-CON.(100~220)uF.(2,2.5,4,6.3)V.20%.D(7.3*4.3*2.7mm).10mOhm SMD.Japan Carlit.SW Series;EE-A030626;11896***8*;TWN	-55°C~105°C	48.7°C	83.7°C	
3	C243	Japan Carlit/SANMOS/SW Series/PC-CON.(100~220)uF.(2,2.5,4,6.3)V.20%.D(7.3*4.3*2.7mm).10mOhm SMD.Japan Carlit.SW Series;EE-A030626;11896***8*;TWN	-55°C~105°C	48.4°C	83.4°C	
4	U23	CYPRESS/W256/IC.SMD.SSOP28P.12Output Buffer.CYPRESS.W256;EE-A040436;14S4025600;TWN	-30°C~100°C	48.8°C	83.8°C	
5	U20	IC.SMD.SO-8P.DualOperational Amplifiers.NS.LMV358M;EE-A030570;14S1035800;TWN	125°C	57.8°C	92.8°C	
6	Q16	APEC/AP9916H/PWR.SMD.TO-252.N-Channel Power MOSFET.APEC.AP9916H;EE-A040445;1315991610;TWN	-25°C~125°C	50.4°C	85.4°C	
7	C155	Japan Carlit/SANMOS/SW Series/PC-CON.(100~220)uF.(2,2.5,4,6.3)V.20%.D(7.3*4.3*2.7mm).10mOhm SMD.Japan Carlit.SW Series;EE-A030626;11896***8*;TWN	-55°C~105°C	48.7°C	83.7°C	
8	U19	(TF)IC.SMD SOP.8Pin Switching PWM Controller.Intersil.ISL6520ACBZ;EE-A020421;14S2652000;TWN	-15°C~100°C	50.2°C	85.2°C	
9	Q13	APEC/AP9916H/PWR.SMD.TO-252.N-Channel Power MOSFET.APEC.AP9916H;EE-A040445;1315991610;TWN	-30°C~125°C	52.9°C	87.9°C	
10	Q14	APEC/AP9916H/PWR.SMD.TO-252.N-Channel Power MOSFET.APEC.AP9916H;EE-A040445;1315991610;TWN	-30°C~125°C	52.9°C	87.9°C	
11	C66	KO-CAP.330uF.6.3V.20%.D(7.3*4.3*2.8mm).45mOhm SMD.KEMET.T520D337M006AS	105°C	48.5°C	83.5°C	
12						
13						
14						
15		Ambient Temperature		26.6°C		

1. Operation Temperature (°C):
 $T_c(\text{Case temp.}) = T_a(\text{Ambient Temp.}) \pm 30^\circ\text{C} = T_j(\text{Junction Temp.}) \pm 25^\circ\text{C}$

Note: The description in red states which temperature is over the specification of the device.